TOSHIBA TLP251

TOSHIBA Photocoupler GaAlAs Ired & Photo-IC

TLP251

Inverter For Air Conditioner
Induction Heating
Transistor Inverter
Power MOS FET Gate Drive
IGBT Gate Drive

The TOSHIBA TLP251 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

TLP251 is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of "direct" gate drive of lower power IGBTs. (~15A)

- Input threshold current: IF=5mA(max.)
- Supply current (I_{CC}): 11mA(max.)
- Supply voltage (V_{CC}): 10–35V
- Output current (I_O): ±0.4A(max.)
- Switching time (t_{pLH} / t_{pHL}): 1µs(max.)
- Isolation voltage: 2500Vrms(min.)
- UL recognized: UL1577, file no.E67349
- Option(D4)

VDE Approved: DIN EN60747-5-2

Maximum Operating Insulation Voltage: 890VPK Highest Permissible Over Voltage: 4000VPK

(Note):When a EN60747-5-2 approved type is needed, Please designate "Option(D4)"

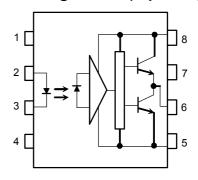
Truth Table

		Tr1	Tr2		
Input	On	On	Off		
LED	Off	Off	On		

Unit in mm 8 7 6 5 90 + 44 9.66 ± 0.25 9.66 ± 0.25 9.66 ± 0.25 9.60 ± 0.25 9.

Weight: 0.54g(typ.)

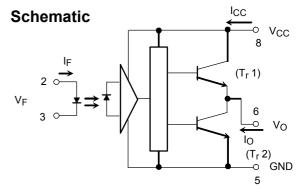
Pin Configuration (top view)



1 : N.C. 5 : GND 2 : Anode 6 : V_O (Output) 3 : Cathode 7 : N.C.

8: V_{CC}

4: N.C.



A $0.1\mu F$ bypass capcitor must be connected between pin 8 and 5(see Note 5).

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
	Forward current	l _F	20	mA	
	Forward current derating	(Ta ≥ 70°C)	ΔI _F / ΔTa	- 0.36	mA / °C
Peak transient forward curi		(Note 1)	I _{FPT}	1	Α
	Reverse voltage		V _R	5	V
	Junction temperature		Tj	125	°C
	"H" peak output current (P _W ≤ 2.0μs, f ≤ 15kHz)	Іорн	- 0.4	А	
	"L" peak output current (P _W ≤ 2.0μs, f ≤ 15kHz)	(Note 2)	lopl	0.4	A
Detector	Output voltage	(Ta ≤ 70°C) (Ta = 85°C)	Vo	35 24	V
De	Supply voltage	(Ta ≤ 70°C) (Ta = 85°C)	Vcc	35 24	V
	Output voltage derating (Ta ≥ 70°C)		ΔV _O / ΔTa	- 0.73	V/°C
	Supply voltage derating (Ta ≥ 70°C)		ΔV _{CC} / ΔΤα	-0.73	V/°C
	Junction temperature		Тј	125	°C
Oper	ating frequency	f	25	kHz	
Oper	rating temperature range	T _{opr}	-20~85	°C	
	age temperature range	T _{stg}	−55~125	°C	
	soldering temperature(10s)	T _{sol}	260	°C	
	Isolation voltage (AC, 1min., R.H.≤ 60%) (Note 4)			2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Pulse width $P_W \le 1\mu s$, 300pps
- Note 2: Expornential waveform
- Note 3: Expornential waveform, $I_{OPH} \le -0.25A (\le 2.0 \mu s)$, $I_{OPL} \le +0.25A (\le 2.0 \mu s)$
- Note 4: Device considerd a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
- Note 5: A ceramic capacitor(0.1µF)should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear ampifier. Failure to provide the bypassing may impair the swiching property. The total lead length between capacitor and coupler should not exceed 1cm.

Recommended Operating Conditions

Characteristic		Symbol	Min.	Тур.	Max.		Unit
Input current, on	(Note6)	I _{F(ON)}	7	8	10		mA
Input voltage, off		V _{F(OFF)}	0	_	0.8		V
Supply voltage		V _{CC}	10	_	30	20	V
Peak output current		I _{OPH} / I _{OPL}	_	-	±0.1		Α
Operating temperature		T _{opr}	-20	25	70	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 6: Input signal rise time(fall time)<0.5μs.

Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Typ.*	Max.	Unit	
Input forward voltage		V _F	_	I _F = 10 mA , Ta = 25°C	a	1.6	1.8	V	
Temperature coefficier voltage	Temperature coefficient of forward voltage		_	I _F = 10 mA	/N	-2.0	_	mV / °C	
Input reverse current		I _R	_	V _R = 5V, Ta = 25°C	27.	_	10	μA	
Input capacitance		C _T	_	V = 0 , f = 1MHz , Ta = 25°C	_	45	250	pF	
Output current	"H" level	Іорн	1	$V_{CC}=30V$ $I_F=10mA$ $V_{8-6}=4V$	-0.1	-0.25	_		
	"L" level	lopl	2	(*1) $I_F = 0$ $V_{6-5} = 2.5V$	0.1	0.2	_	A	
Outsuturallana	"H" level	Voh	3	V_{CC1} = +15V, V_{EE1} = -15V R_L = 200 Ω , I_F = 5mA	11	13.2	_	.,,	
Output voltage	"L" level	V _{OL}	4	V_{CC1} = +15V, V_{EE1} = -15V R_L = 200 Ω , V_F = 0.8V	_	-14.5	-12.5	V	
	"H" level	Іссн	_	V _{CC} = 30V, I _F = 10mA Ta = 25°C	_	7.5	_		
Complete accompany				V _{CC} = 30V, I _F = 10mA	_	_	11	- mA	
Supply current	"L" level	I _{CCL}	_	V _{CC} = 30V, I _F = 0mA Ta = 25°C	_	8	_	IIIA	
				V _{CC} = 30V, I _F = 0mA	_	_	11		
Threshould input current	"Output $L \rightarrow H$ "	I _{FLH}	_	$V_{CC1} = +15V, V_{EE1} = -15V$ $R_L = 200\Omega, V_O > 0V$	_	1.2	5	mA	
Threshold input voltage	"Output $H \rightarrow L$ "	V _{FHL}	_	V_{CC1} = +15V, V_{EE1} = -15V R_L = 200 Ω , V_O < 0V	0.8	_	_	٧	
Supply voltage		V _{CC}	_		10	_	35	V	
Capacitance (input-output)		Cs	_	Vs = 0 , f = 1MHz Ta = 25°C	_	1.0	2.0	pF	
Resistance (input-output)		R _s	_	Vs = 500V, Ta = 25°C R.H. ≤ 60%	1×10 ¹²	10 ¹⁴	_	Ω	

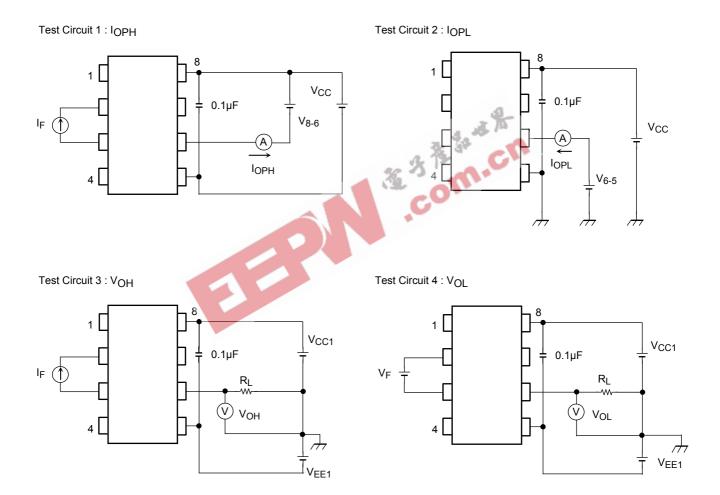
^{*} All typical values are at Ta=25°C

^{(*1):} Duration of I_O time ≤ 50µs

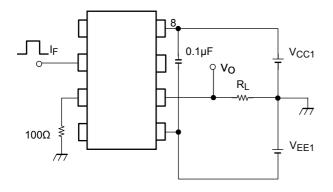
Switching Characteristics (Ta = $-20\sim70$ °C, unless otherwise specified)

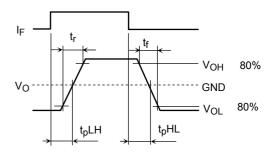
Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Typ.*	Max.	Unit
Propagation	L→H	t _{pLH}	- - 5	I _F = 8mA V _{CC1} = +15V, V _{EE1} = -15V	_	0.25	1.0	116
delay time	H→L	t _{pHL}			_	0.25	1.0	
Output rise time		t _r		$R_L = 200 \Omega$	_	_	_	μs
Output fall time		t _f			_	_	_	
Common mode transient immunity at high level output		C _{MH}	- 6	V _{CM} = 600V, I _F = 8mA, V _{CC} = 30V, Ta = 25°C	-5000	_	_	V / µs
Common mode transient immunity at low level output		C _{ML}		V _{CM} = 600V, I _F = 0mA, V _{CC} = 30V, Ta = 25°C	5000	_	_	V / µs

^{*}All typical values are at Ta=25°C

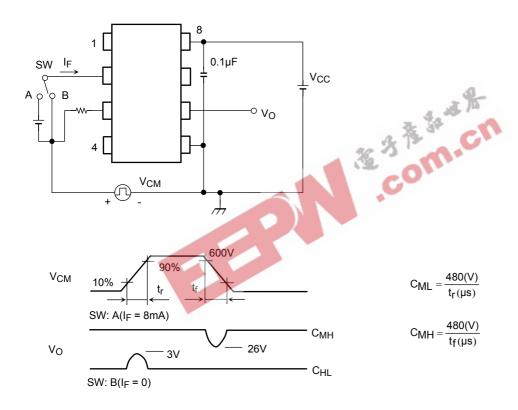


Test Circuit 5: t_{pLH}, t_{pHL}, t_r, t_f



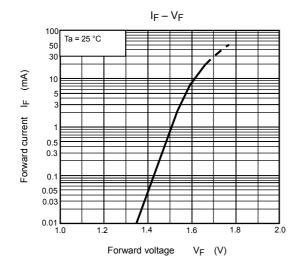


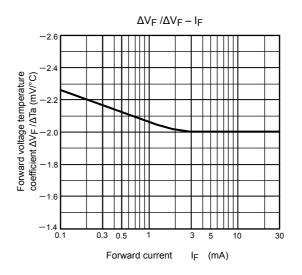
Test Circuit 6: C_{MH}, C_{ML}

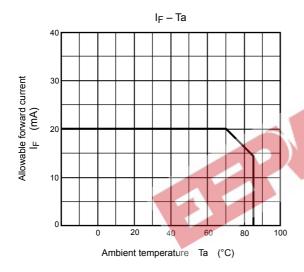


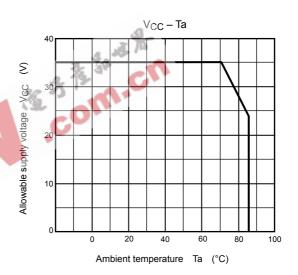
 C_{ML} (C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

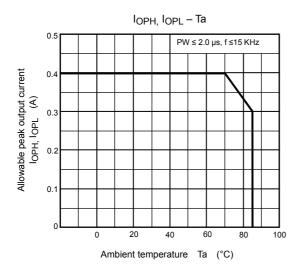
5











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